

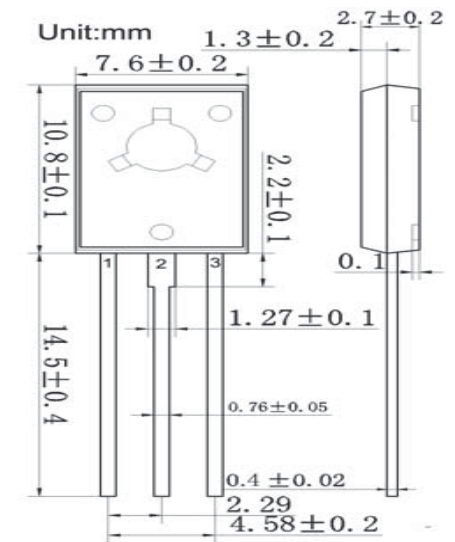
TO-126 Plastic-Encapsulate Transistors

**FEATURES**

- High Forward Current Transfer Ratio  $h_{FE}$  Which has Satisfactory Linearity
- Low Collector-Emitter Saturation Voltage  $V_{CE(sat)}$
- TRANSISTOR (PNP)

**MECHANICAL DATA**

- Case style:TO-126 molded plastic
- Mounting position:any



/ÄK'5536\*\* -Ä@#'''3(5#6\* QÄ14 3

**MAXIMUM RATINGS AND CHARACTERISTICS**

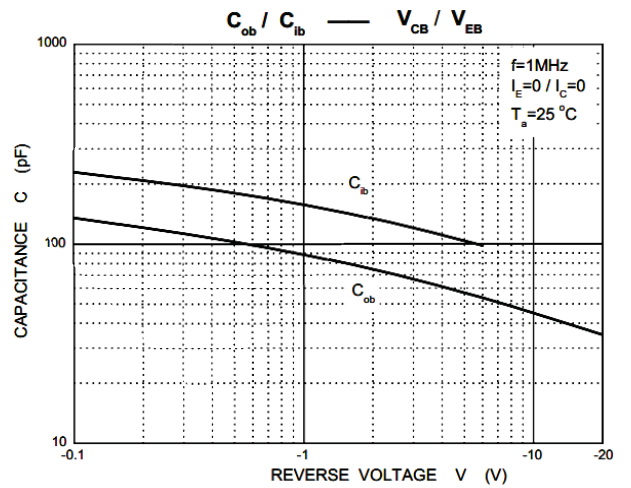
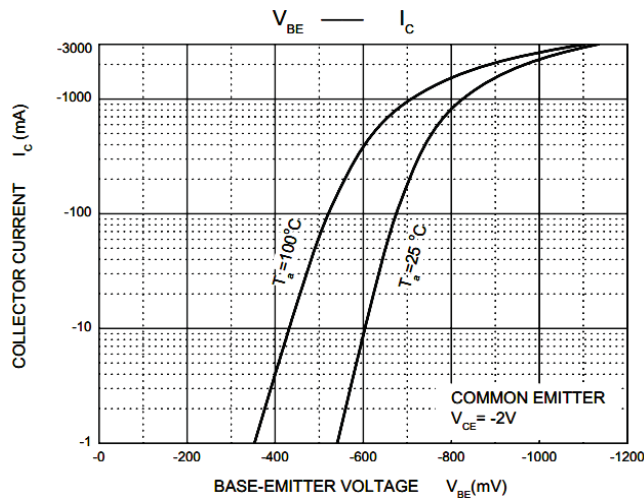
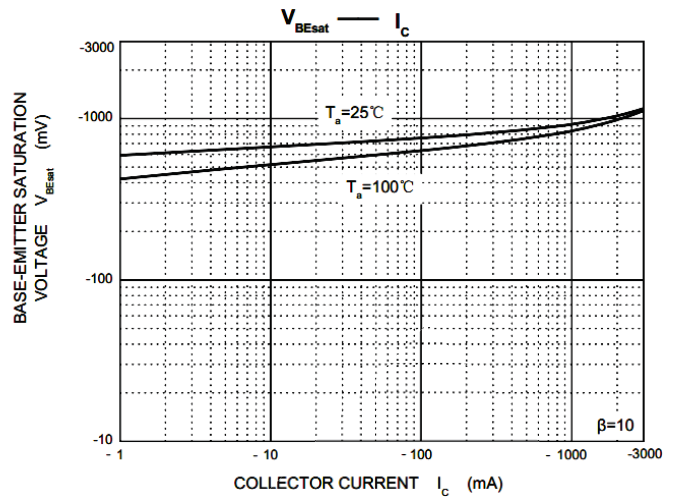
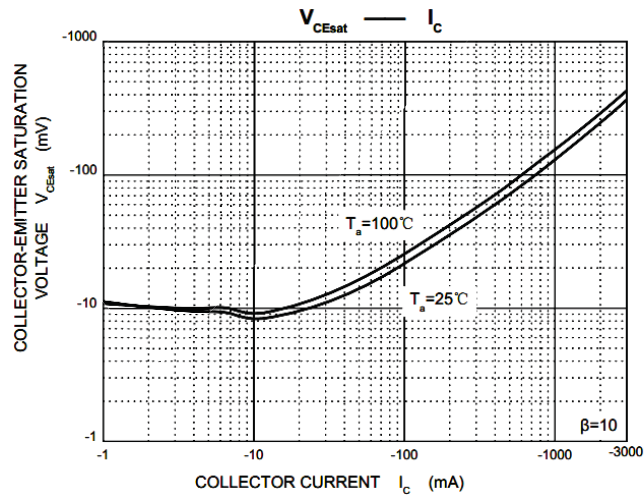
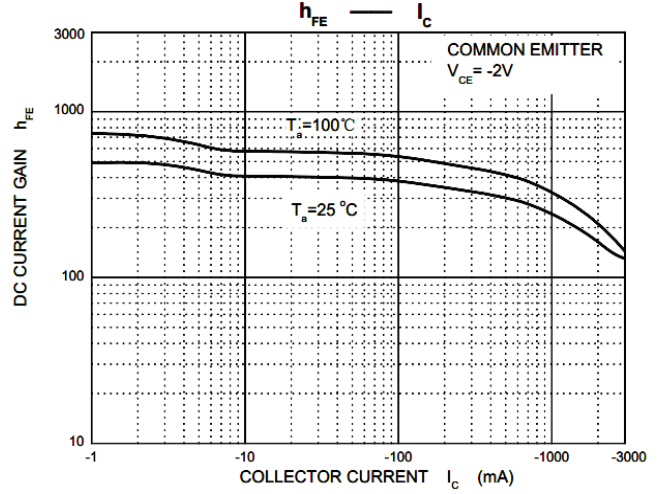
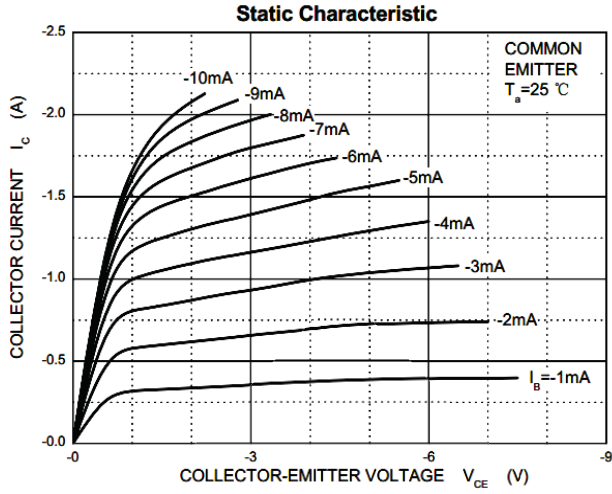
@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	-40	V
Collector Emitter Voltage	$V_{CEO}$	-30	V
Emitter Base Voltage	$V_{EBO}$	-6	V
Collector Current	$I_C$	-3	A
Collector Power Dissipation	$P_C$	1.25	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	100	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	- 55 to +150	°C

**MOSFET ELECTRICAL CHARACTERISTICS**  $T_A=25^\circ C$  unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-6			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$			-1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -30V, I_B = 0$			-10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -6V, I_C = 0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -2V, I_C = -1A$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2A, I_B = -0.2A$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2A, I_B = -0.2A$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -5V, I_C = -0.1A, f = 10MHz$	50	80		MHz

# RATINGS AND CHARACTERISTIC CURVES



## RATINGS AND CHARACTERISTIC CURVES

